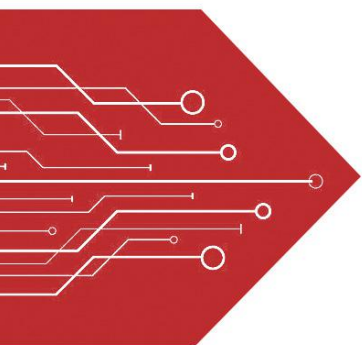


MSKSEMI

SEMICONDUCTOR



ESD



TVS



TSS



MOV

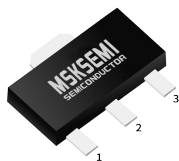


GDT



PLED

Product data sheet



1. BASE

2. COLLECTOR

3. EMITTER

TRANSISTOR (PNP)

FEATURES

Low speed switching

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-3	A
P_C	Collector Power Dissipation	0.5	W
$R_{\theta JA}$	Thermal Resistance, junction to Ambient	250	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

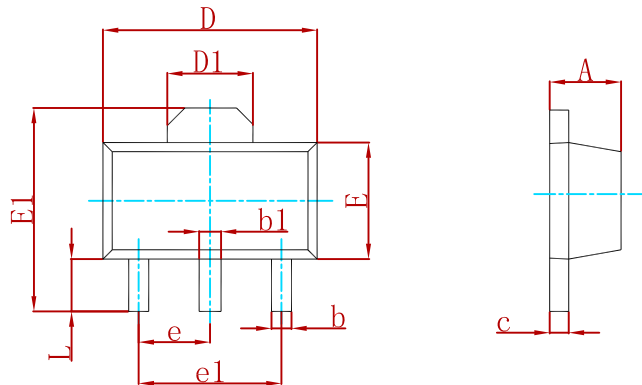
ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}$, $I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}$, $I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}$, $I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-40\text{V}$, $I_E=0$			-1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-30\text{V}$, $I_B=0$			-10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-6\text{V}$, $I_C=0$			-1	μA
DC current gain	h_{FE}	$V_{CE}=-2\text{V}$, $I_C=-1\text{A}$	60		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2\text{A}$, $I_B=-0.2\text{A}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-2\text{A}$, $I_B=-0.2\text{A}$			-1.5	V
Transition frequency	f_T	$V_{CE}=-5\text{V}$, $I_C=-0.1\text{A}$ $f=10\text{MHz}$		80		MHz

CLASSIFICATION OF h_{FE}

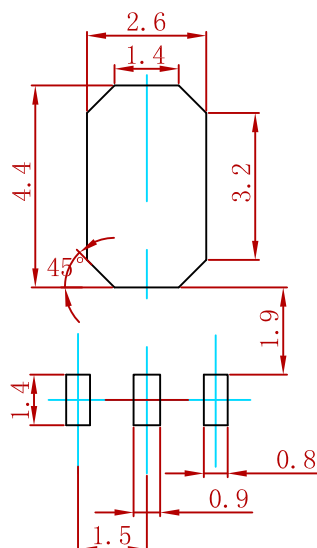
Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

Suggested Pad Layout



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.05 mm.
 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
2SB772-MS	SOT-89	1000

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